
2SJ526

Silicon P Channel MOS FET
High Speed Power Switching

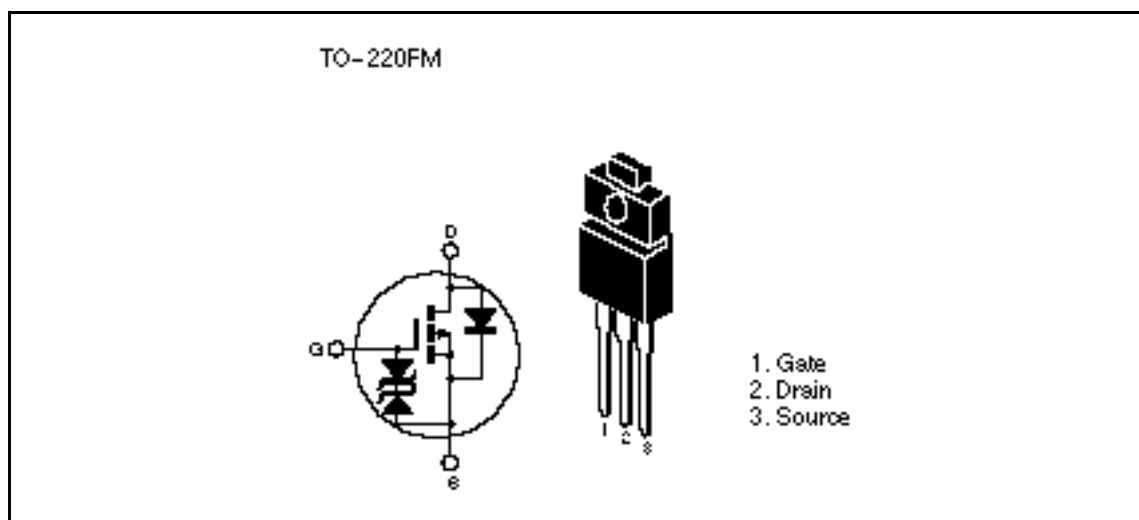
HITACHI

ADE-208-579C (Z)
4th. Edition
Jun 1998

Features

- Σ Low on-resistance
 $R_{DS(on)} = 0.11 \text{ W typ.}$
- Σ Low drive current
- Σ 4 V gate drive devices
- Σ High speed switching

Outline



2SJ526

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	-60	V
Gate to source voltage	V_{GS}	±20	V
Drain current	I_D	-12	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	-48	A
Body-drain diode reverse drain current	I_{DR}	-12	A
Avalanche current	I_{AP} ^{Note3}	-12	A
Avalanche energy	E_{AR} ^{Note3}	12	mJ
Channel dissipation	P_{ch} ^{Note2}	25	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

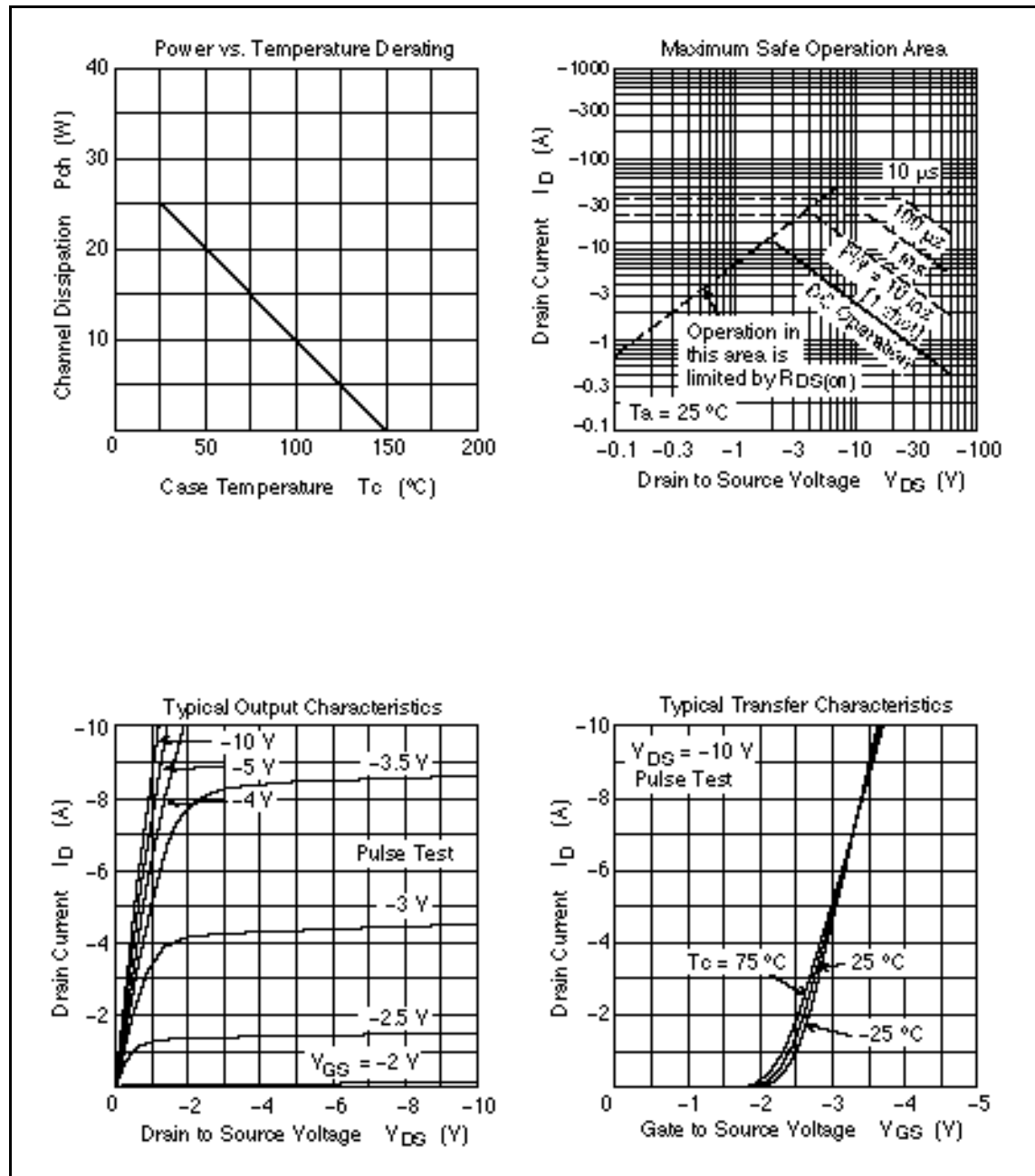
Note: 1. PW ≤ 10ms, duty cycle ≤ 1 %
 2. Value at Tc = 25°C
 3. Value at Tch = 25°C, Rg ≥ 50 W

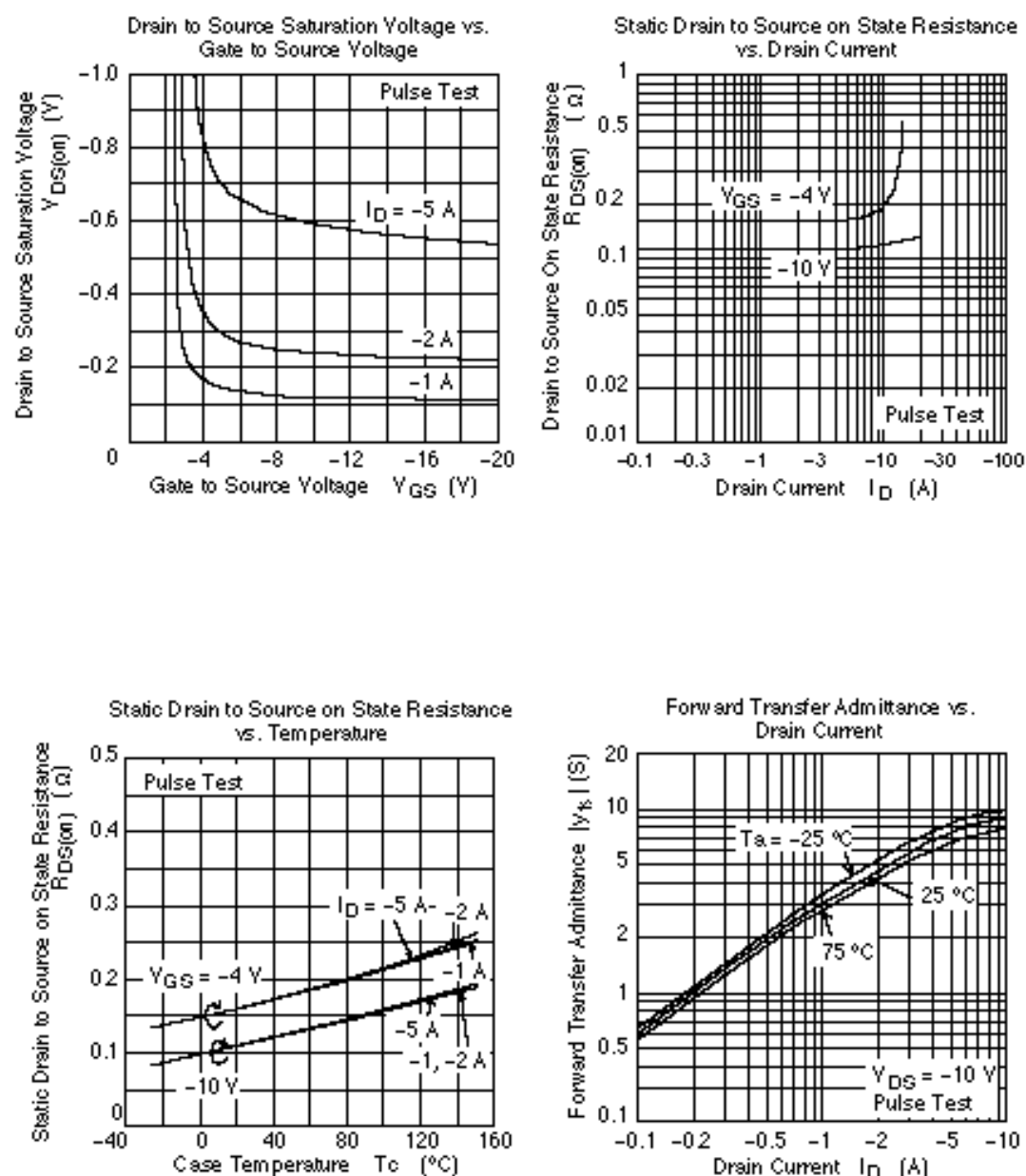
Electrical Characteristics (Ta = 25°C)

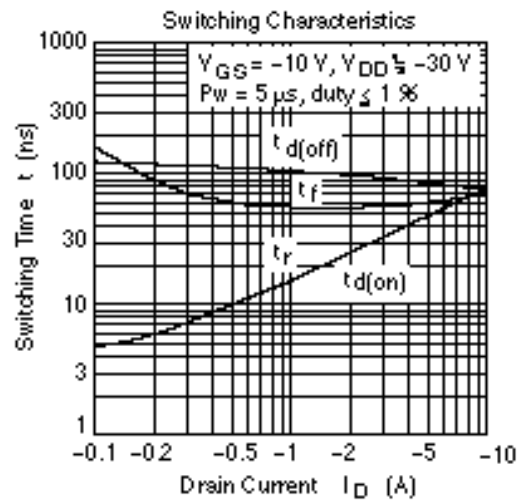
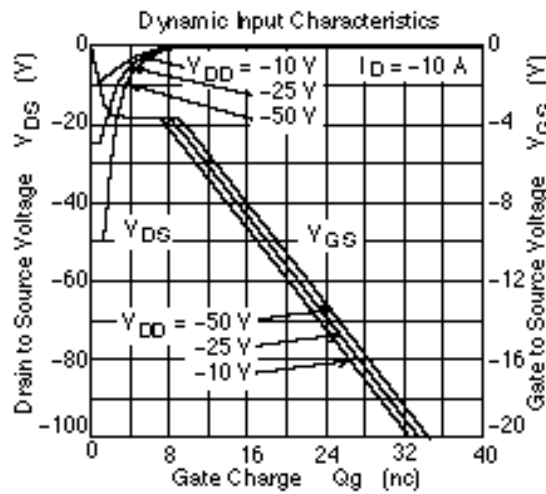
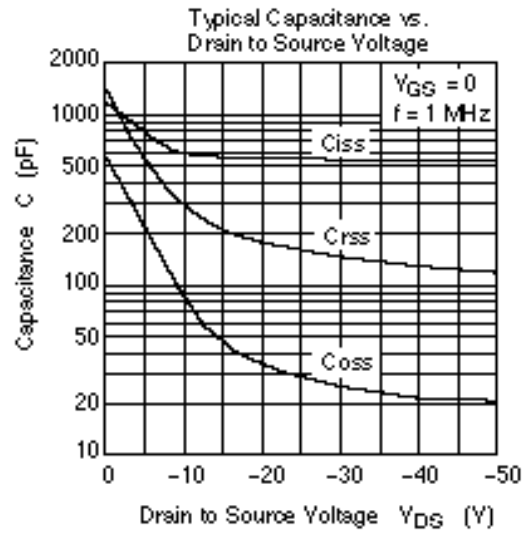
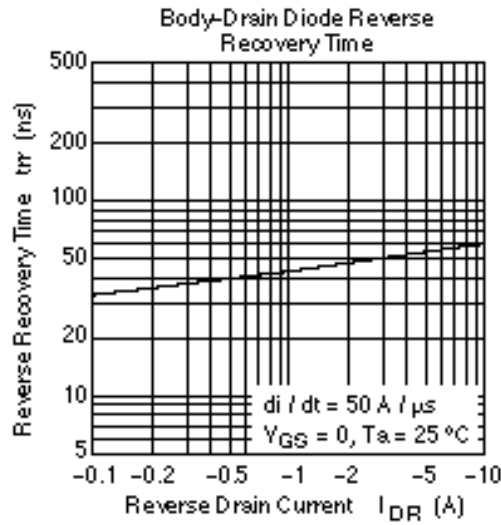
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-60	—	—	V	$I_D = -10mA$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = ±100mA$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-10	mA	$V_{DS} = -60V$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	mA	$V_{GS} = ±16V$, $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.0	V	$I_D = -1mA$, $V_{DS} = -10V$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.11	0.15	W	$I_D = -6A$, $V_{GS} = -10V$ ^{Note4}
	$R_{DS(on)}$	—	0.16	0.23	W	$I_D = -6A$, $V_{GS} = -4V$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	5	8	—	S	$I_D = -6A$, $V_{DS} = -10V$ ^{Note4}
Input capacitance	C_{iss}	—	580	—	pF	$V_{DS} = -10V$
Output capacitance	C_{oss}	—	300	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	85	—	pF	f = 1MHz
Turn-on delay time	$t_{d(on)}$	—	10	—	ns	$V_{GS} = -10V$, $I_D = -6A$
Rise time	t_r	—	55	—	ns	$R_L = 6W$
Turn-off delay time	$t_{d(off)}$	—	85	—	ns	
Fall time	t_f	—	60	—	ns	
Body-drain diode forward voltage	V_{DF}	—	-1.2	—	V	$I_F = -12A$, $V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	60	—	ns	$I_F = -12A$, $V_{GS} = 0$ diF/ dt = 50A/μs

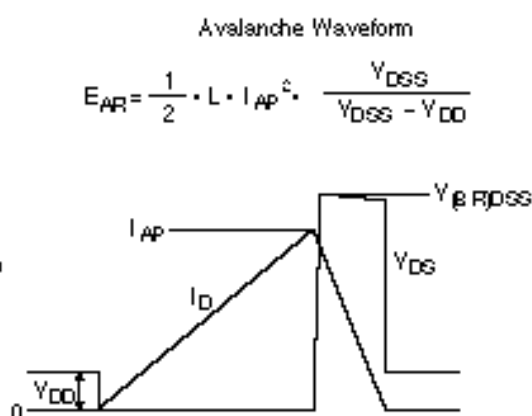
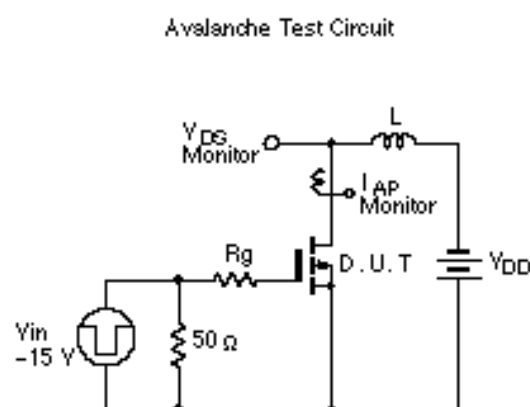
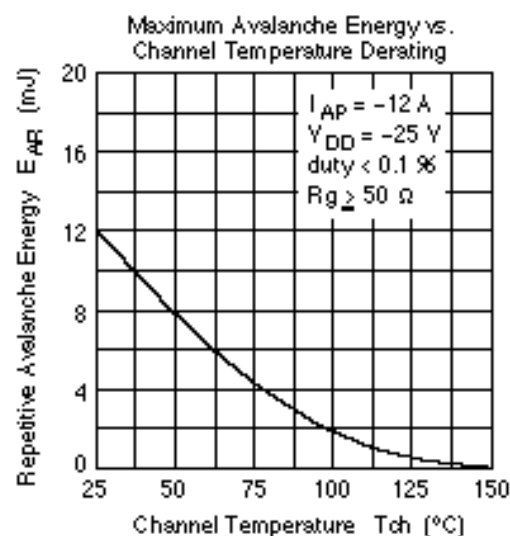
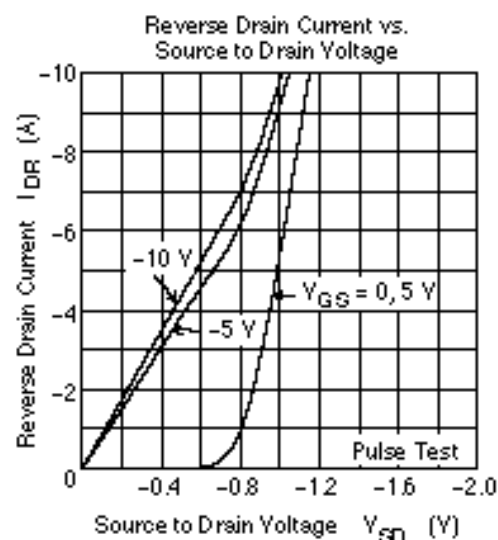
Note: 4. Pulse test

Main Characteristics

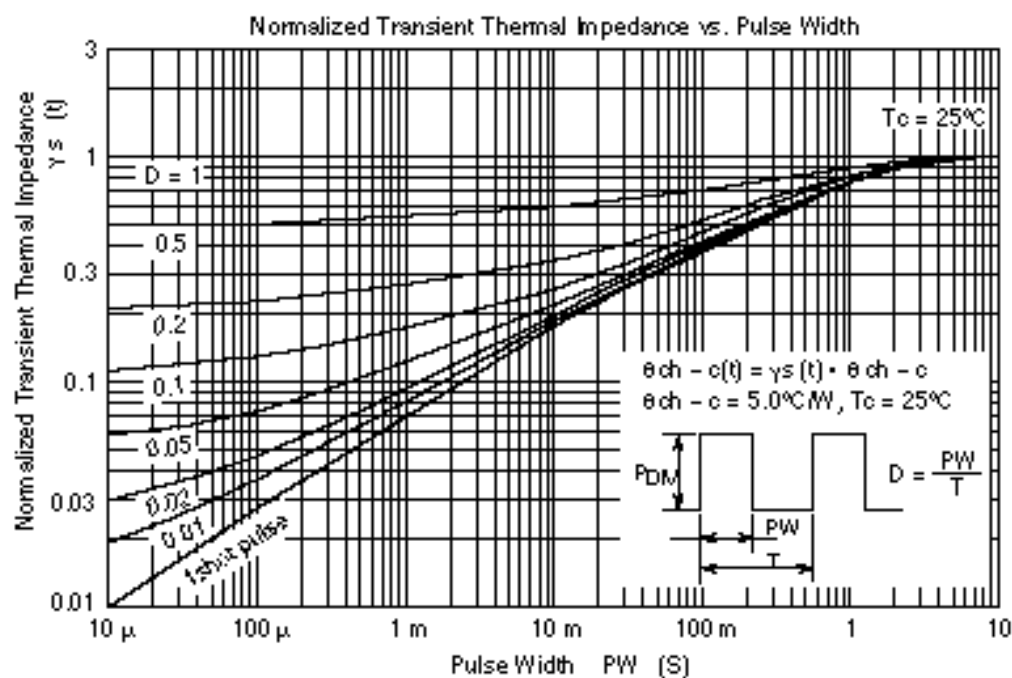




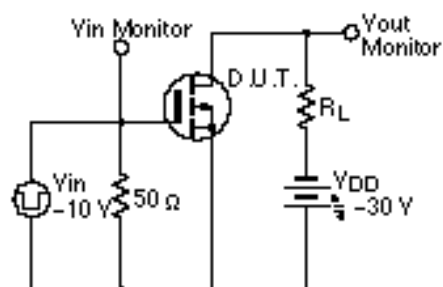




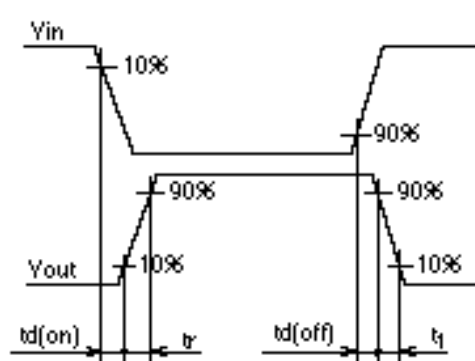
$$E_{AR} = \frac{1}{2} \cdot L \cdot I_{AP}^2 \cdot \frac{V_{DS}}{V_{DS} - V_{DD}}$$



Switching Time Test Circuit



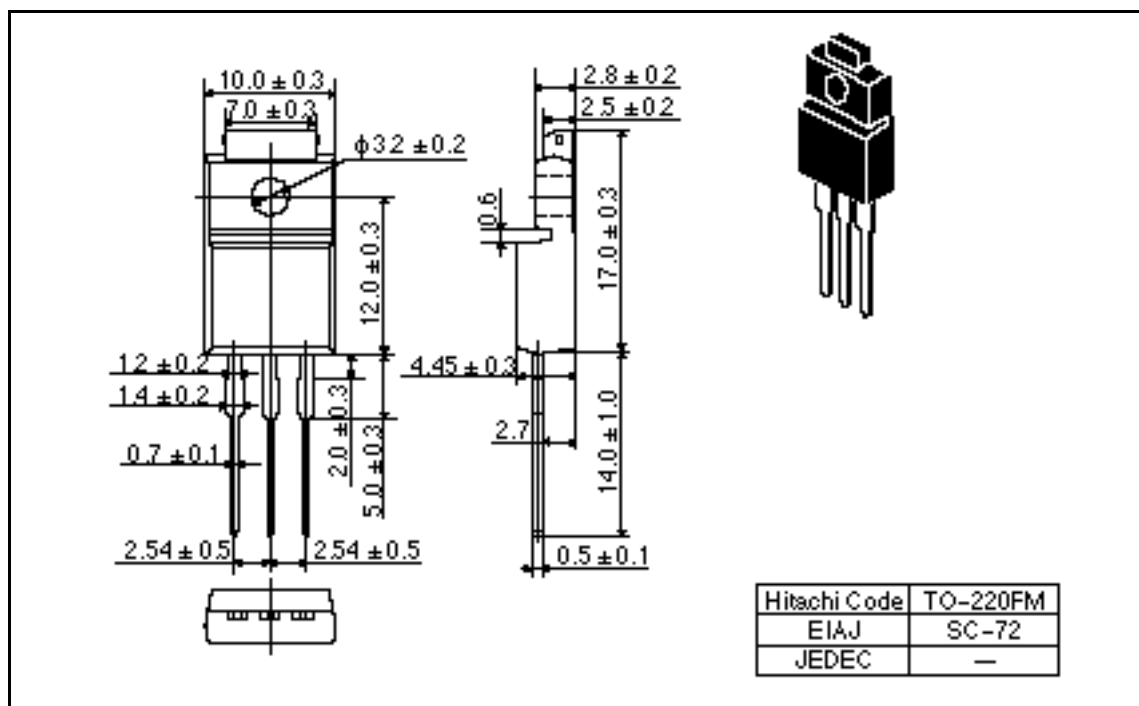
Waveform



2SJ526

Package Dimensions

Unit: mm



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